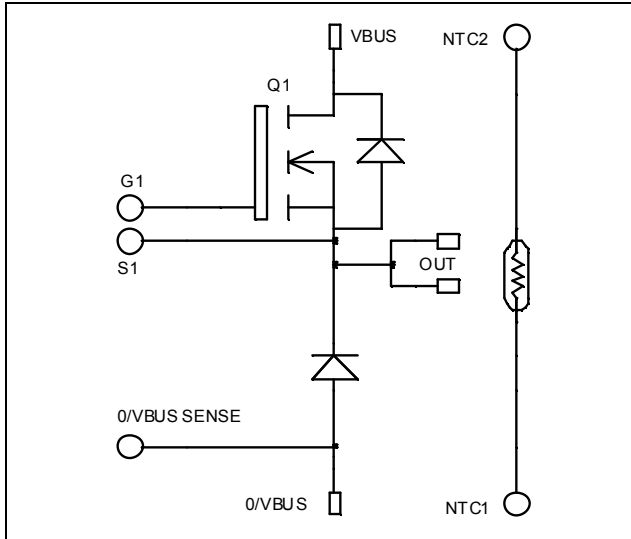


## Buck chopper MOSFET Power Module

$V_{DSS} = 200V$   
 $R_{DSon} = 8m\Omega$  typ @  $T_j = 25^\circ C$   
 $I_D = 208A$  @  $T_c = 25^\circ C$

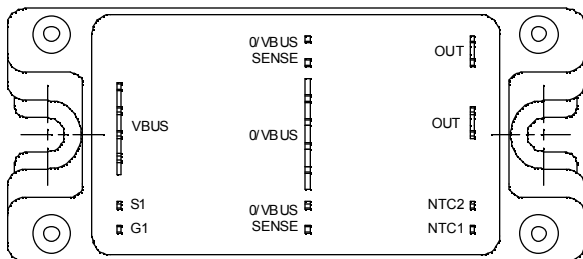


### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration




### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
$V_{DSS}$	Drain - Source Breakdown Voltage	200	V	
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	A	
		$T_c = 80^\circ C$		155
$I_{DM}$	Pulsed Drain current	832		
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V	
$R_{DSon}$	Drain - Source ON Resistance	10	$m\Omega$	
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	781	W
$I_{AR}$	Avalanche current (repetitive and non repetitive)	100	A	
$E_{AR}$	Repetitive Avalanche Energy	50	mJ	
$E_{AS}$	Single Pulse Avalanche Energy	3000		


**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 200\text{V}$			375	$\mu\text{A}$
		$V_{GS} = 0\text{V}, V_{DS} = 160\text{V}$			1500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 104\text{A}$		8	10	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$	3		5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			$\pm 150$	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$		14.4		nF
$C_{oss}$	Output Capacitance	$V_{DS} = 25\text{V}$		4.66		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.29		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$		280		nC
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 100\text{V}$		106		
$Q_{gd}$	Gate – Drain Charge	$I_D = 208\text{A}$		134		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15\text{V}$ $V_{Bus} = 133\text{V}$ $I_D = 208\text{A}$ $R_G = 2.5\Omega$		32		ns
$T_r$	Rise Time			64		
$T_{d(off)}$	Turn-off Delay Time			88		
$T_f$	Fall Time			116		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15\text{V}, V_{Bus} = 133\text{V}$ $I_D = 208\text{A}, R_G = 2.5\Omega$		1698		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			1858		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15\text{V}, V_{Bus} = 133\text{V}$ $I_D = 208\text{A}, R_G = 2.5\Omega$		1872		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			1972		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$		500	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		750	
$I_F$	DC Forward Current			180		A
$V_F$	Diode Forward Voltage	$I_F = 180\text{A}$		1.1	1.15	V
		$I_F = 360\text{A}$		1.4		
		$I_F = 180\text{A}$	$T_j = 125^\circ\text{C}$	0.9		
$t_{rr}$	Reverse Recovery Time	$I_F = 180\text{A}$ $V_R = 133\text{V}$ $di/dt = 600\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	31		ns
			$T_j = 125^\circ\text{C}$	60		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 180\text{A}$ $V_R = 133\text{V}$ $di/dt = 600\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	180		nC
			$T_j = 125^\circ\text{C}$	750		

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	Transistor		0.16	°C/W	
		Diode		0.32		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

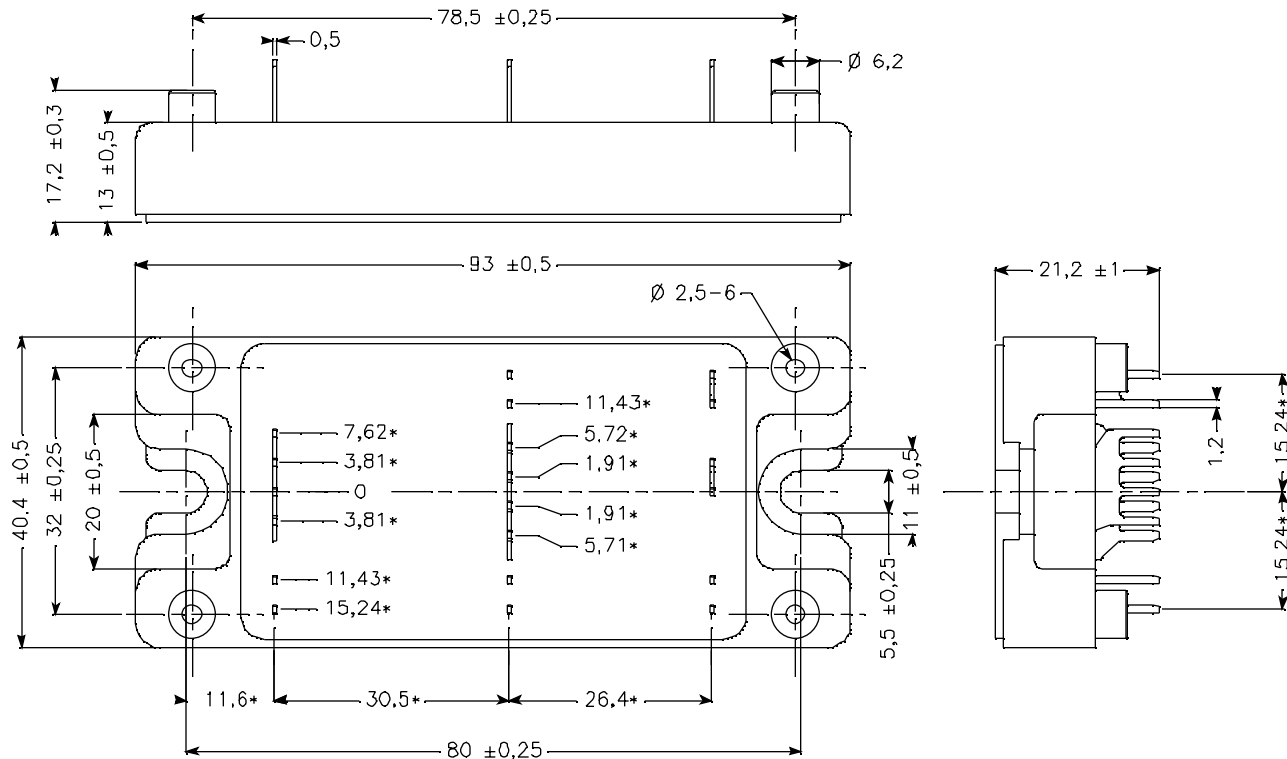
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

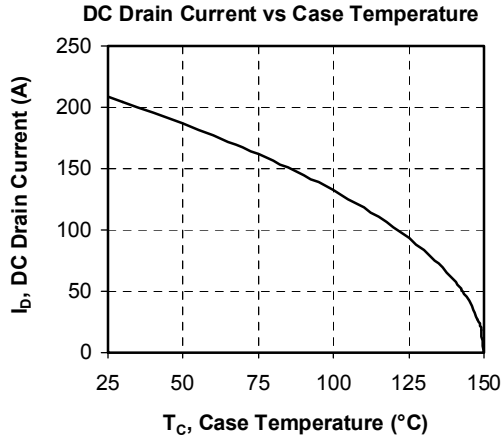
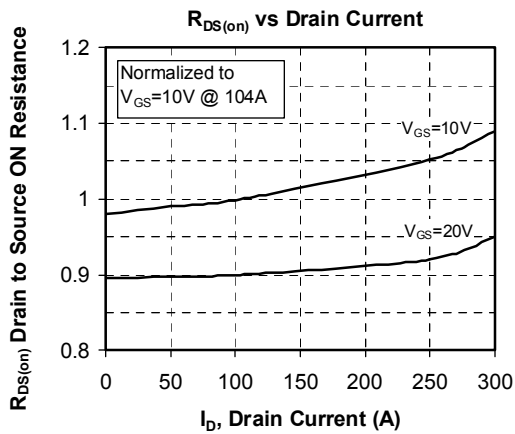
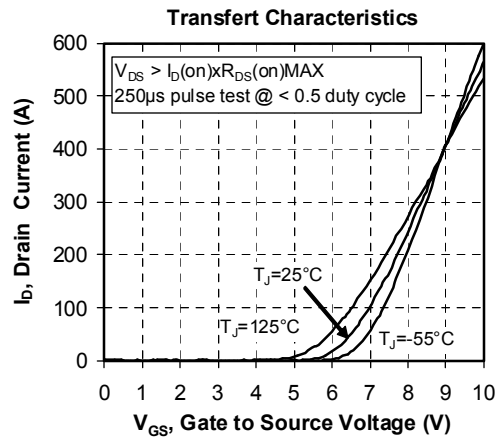
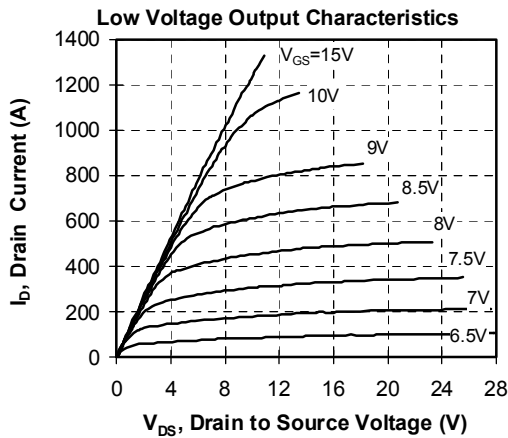
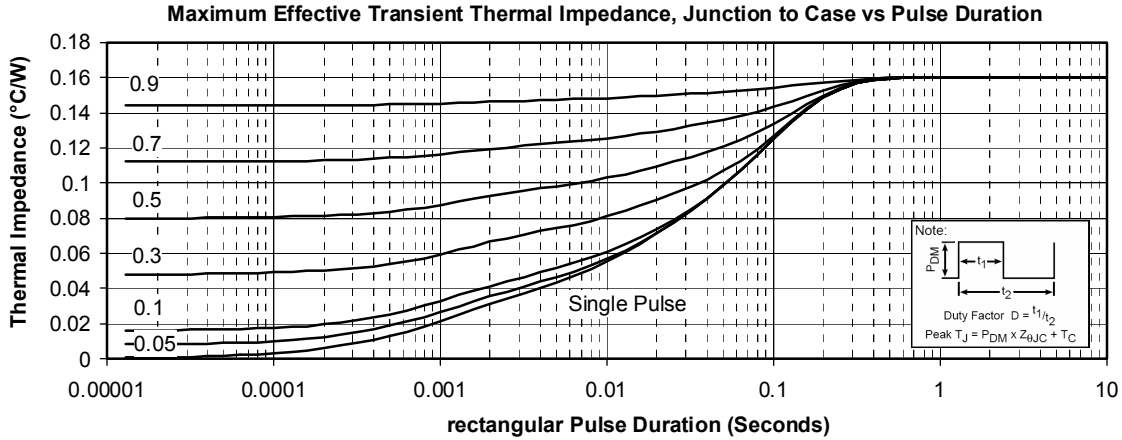
## SP4 Package outline (dimensions in mm)

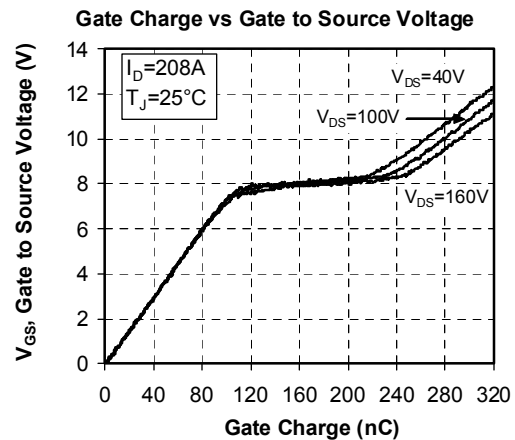
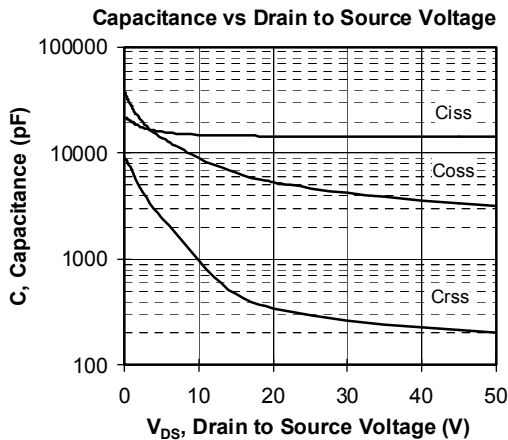
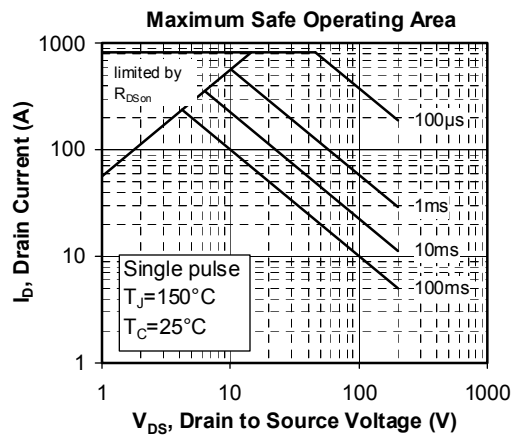
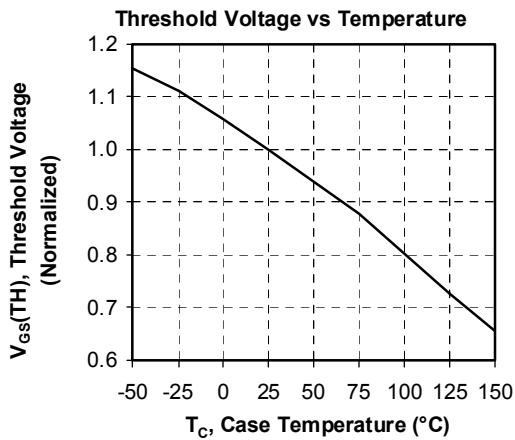
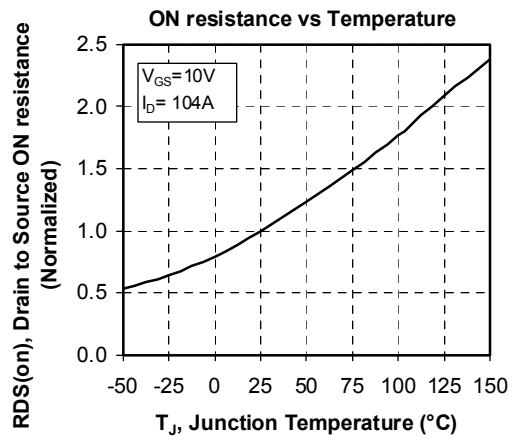
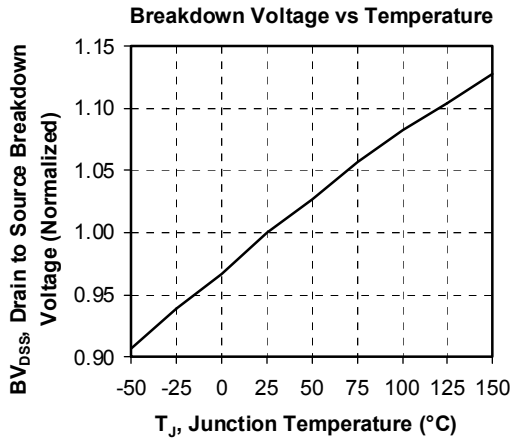


ALL DIMENSIONS MARKED "\*" ARE TOLERENCED AS:  $\boxed{\oplus \ominus 0.1}$

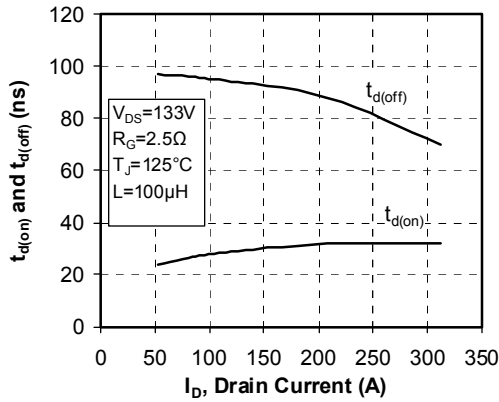
See application note APT0501 - Mounting Instructions for SP4 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve

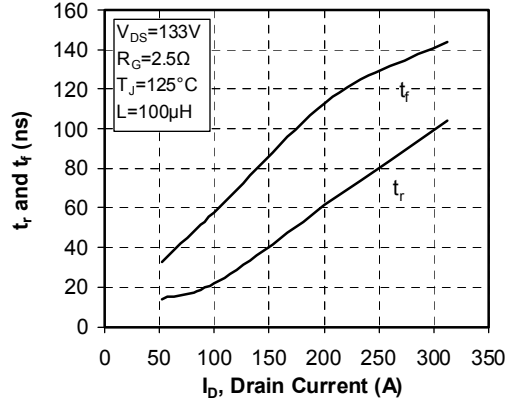




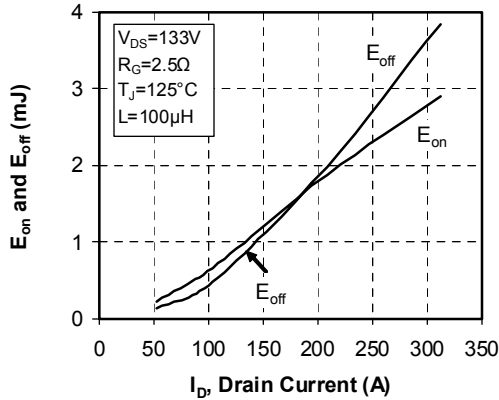
**Delay Times vs Current**



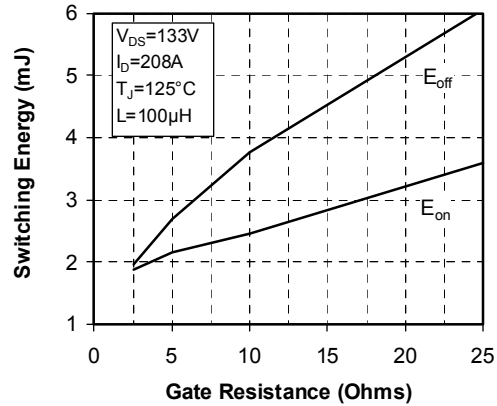
**Rise and Fall times vs Current**



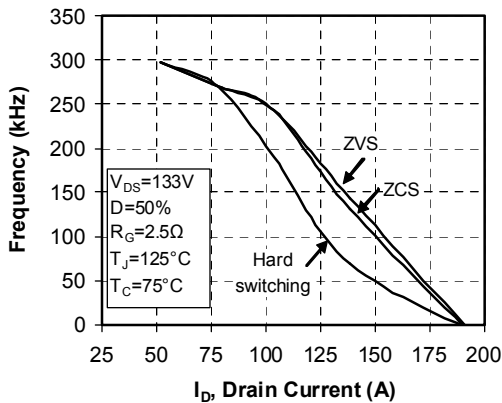
**Switching Energy vs Current**



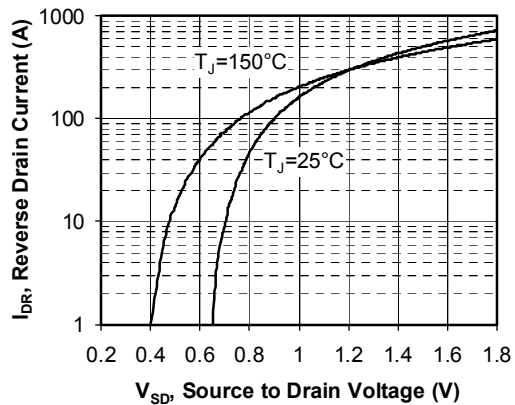
**Switching Energy vs Gate Resistance**



**Operating Frequency vs Drain Current**



**Source to Drain Diode Forward Voltage**



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